PROCESS CPD30V

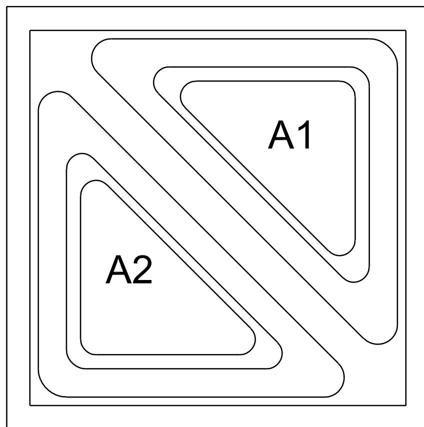
Dual Switching Diode

Dual, Common Cathode,
High Speed Switching Diode Chip

PROCESS DETAILS

Die Size	15.4 x 15.4 MILS
Die Thickness	7.1 MILS
Anode 1 Bonding Pad Area	5.9 x 5.9 x 8.3 MILS
Anode 2 Bonding Pad Area	5.9 x 5.9 x 8.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 10,000Å

GEOMETRY



BACKSIDE COMMON CATHODE R0

GROSS DIE PER 4 INCH WAFER
46,200

PRINCIPAL DEVICE TYPE
CMLD2838

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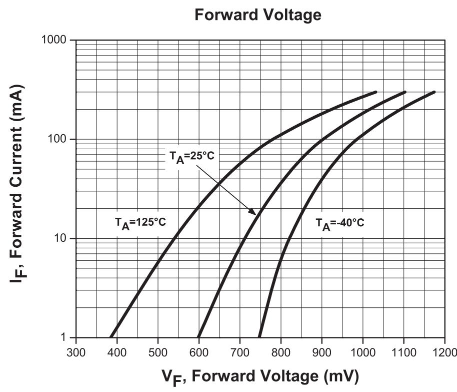
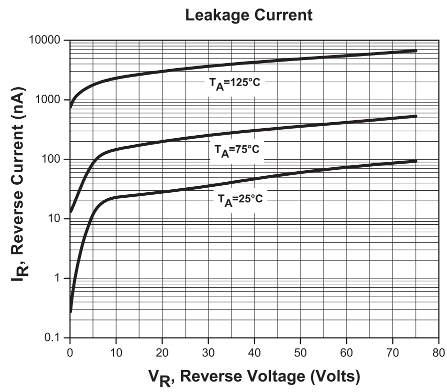
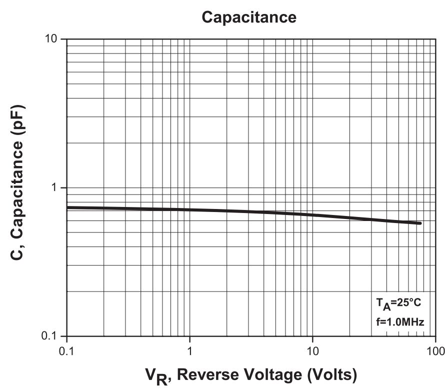
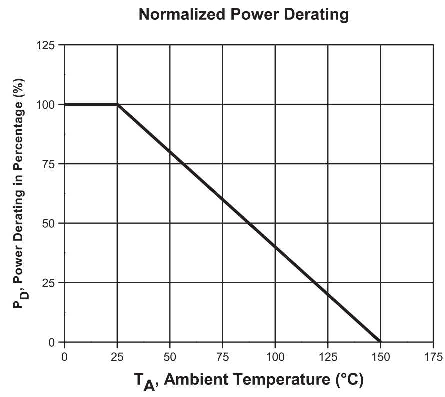
PROCESS CPD30V

Typical Electrical Characteristics









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